2SK2876-01MR

FUJI POWER MOSFET

N-CHANNEL SILICON POWER MOSFET

FAP-2S Series

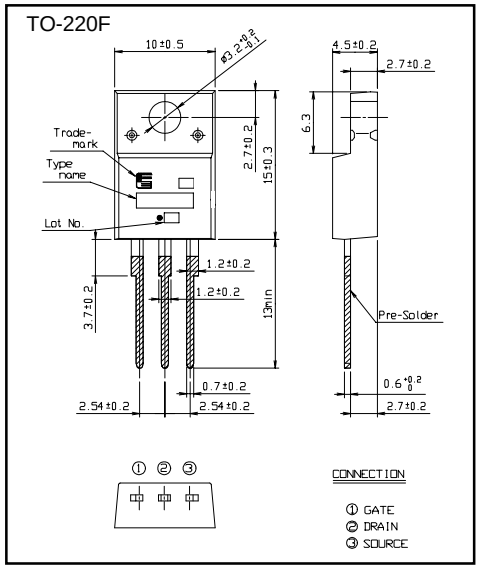
■ Features

- High speed switching
- Low on-resistance
- No secondary breadown
- Low driving power
- Avalanche-proof

■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

■ Outline Drawings



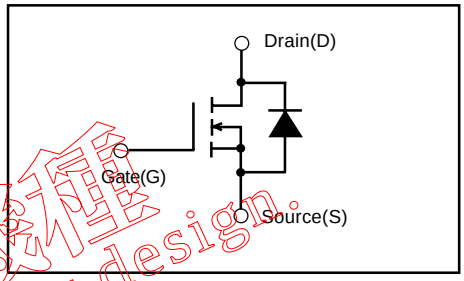
■ Maximum ratings and characteristic Absolute maximum ratings

● (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	500	V
Continuous drain current	I_D	±6	A
Pulsed drain current	$I_{D(puls)}$	±24	A
Gate-source voltage	V_{GS}	±35	V
Repetitive or non-repetitive	I_{AR} *2	6	A
Maximum Avalanche Energy	E_{AS} *1	196.9	mJ
Max. power dissipation	P_D	30	W
Operating and storage	T_{ch}	+150	°C
temperature range	T_{stg}	-55 to +150	°C

*1 L=10.0mH, Vcc=50V *2 Tch≤150°C

■ Equivalent circuit schematic



● Electrical characteristics (T_c =25°C unless otherwise specified)

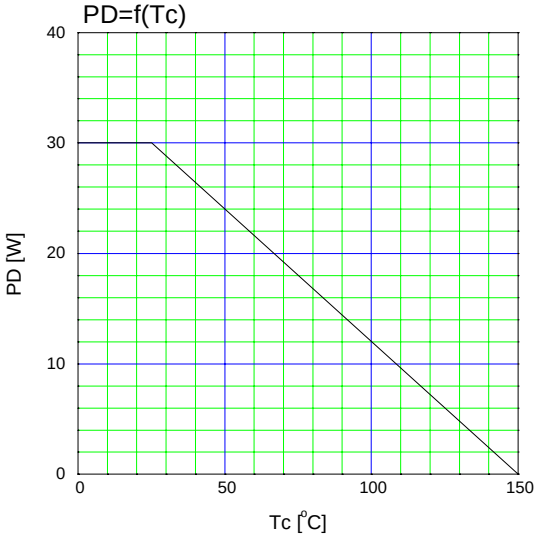
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltaget	$V_{(BR)DSS}$	I_D=1mA V_{GS}=0V		500			V
Gate threshold voltage	$V_{GS(th)}$	I_D=1mA V_{DS}=V_{GS}		3.5	4.0	4.5	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=500V V_{GS}=0V	T_{ch}=25°C		10	500	μA
			T_{ch}=125°C		0.2	1.0	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±35V V_{DS}=0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=3A V_{GS}=10V			1.25	1.5	Ω
Forward transcondutance	g_{fs}	I_D=3A V_{DS}=25V		2	4		S
Input capacitance	C_{iss}	V_{DS}=25V			540	810	pF
Output capacitance	C_{oss}	V_{GS}=0V			100	150	
Reverse transfer capacitance	C_{rss}	f=1MHz			45	70	
Turn-on time t_{on}	$t_{d(on)}$	V_{CC}=300V I_D=6A			13	20	ns
	t_r	V_{GS}=10V			30	45	
Turn-off time t_{off}	$t_{d(off)}$	R_{GS}=10 Ω			40	60	
	t_f				25	40	
Avalanche capability	I_{AV}	L=10.0 mH T_{ch}=25°C		6			A
Diode forward on-voltage	V_{SD}	I_F=2xI_{DR} V_{GS}=0V T_{ch}=25°C			1.0	1.5	V
Reverse recovery time	t_{rr}	I_F=I_{DR} V_{GS}=0V			450		ns
Reverse recovery charge	Q_{rr}	-di/dt=100A/μs T_{ch}=25°C			3.2		μC

● Thermalcharacteristics

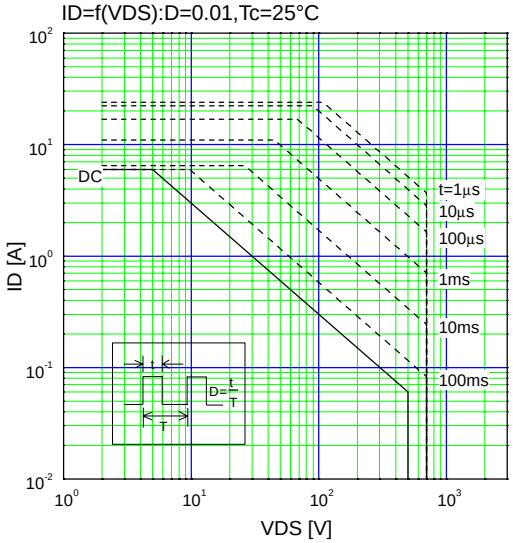
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			4.17	°C/W
	$R_{th(ch-a)}$	channel to ambient			62.5	°C/W

Characteristics

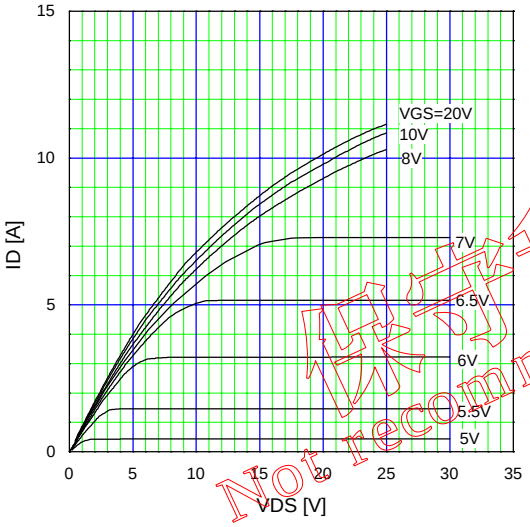
Power Dissipation
PD=f(Tc)



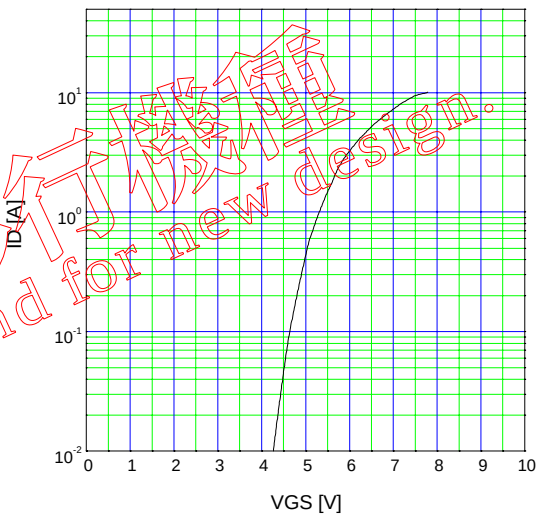
Safe operating area
ID=f(VDS):D=0.01,Tc=25°C



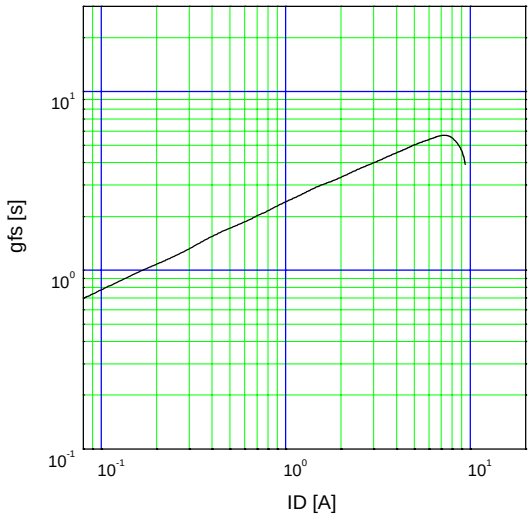
Typical output characteristics
ID=f(VDS):80µs Pulse test,Tch=25°C



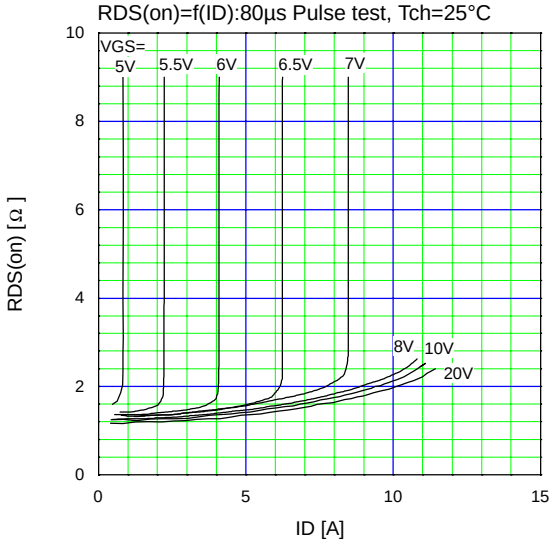
Typical transfer characteristic
ID=f(VGS):80µs Pulse test,VDS=25V,Tch=25°C



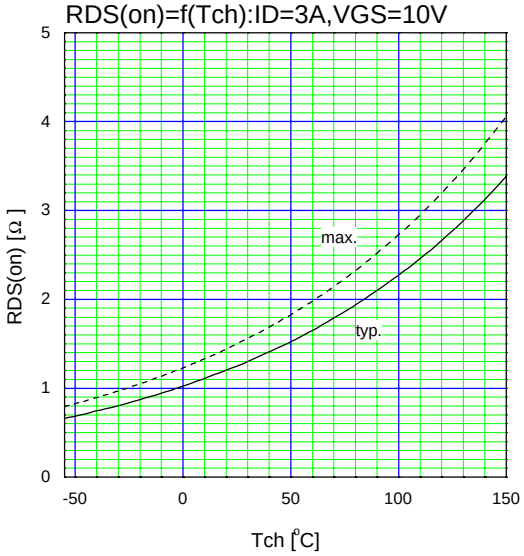
Typical forward transconductance
gfs=f(ID):80µs Pulse test,VDS=25V,Tch=25°C



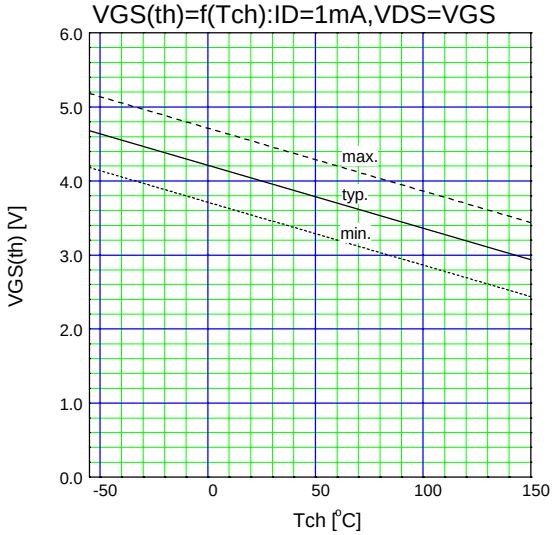
Typical drain-source on-state resistance
RDS(on)=f(ID):80µs Pulse test, Tch=25°C



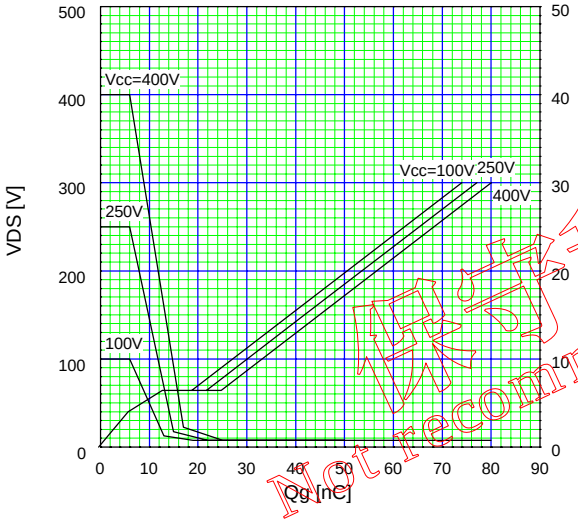
Drain-source on-state resistance
RDS(on)=f(Tch):ID=3A,VGS=10V



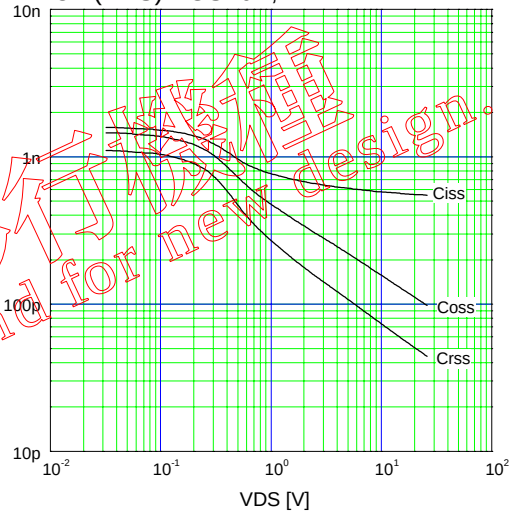
Gate threshold voltage
VGS(th)=f(Tch):ID=1mA,VDS=VGS



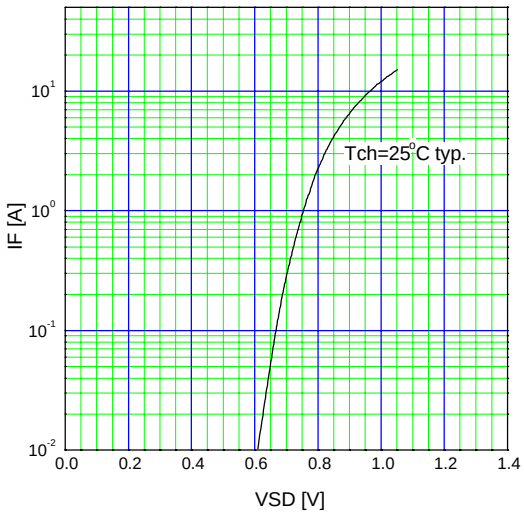
Typical gate charge characteristic
VGS=f(Qg):ID=6A,Tch=25°C



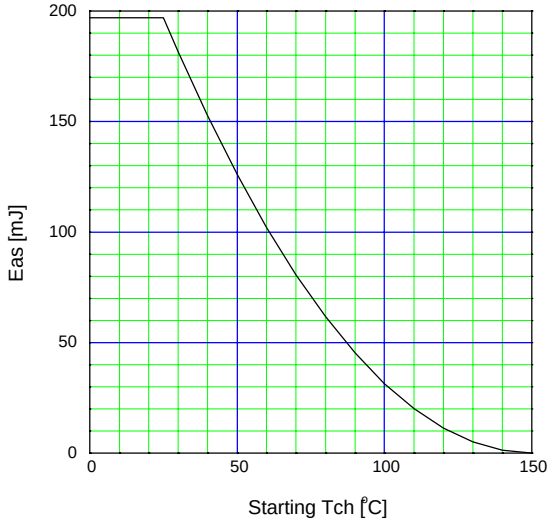
Typical capacitances
C=f(VDS):VGS=0V,f=1MHz



Forward characteristic of reverse of diode
IF=f(VSD):80μs Pulse test,VGS=0V



Avalanche energy derating
Eas=f(starting Tch):Vcc=50V,IAV=6A



Transient thermal impedance
Zthch=f(t) parameter:D=t/T